

Custom No.: 31561
Application No.: 10/707,082
Docket No.: 11690-US-PA

AMENDMENTS

To the Claims:

1. (currently amended) A device for breaking a leakage current path existing in a defect memory cell in a memory array within a memory device, comprising:

a column selection line coupled to a first circuit block and adapted to select a column of a memory cell within a memory array, wherein the first circuit block is capable of outputting a column turn-off signal when the defect memory cell is detected ;

a row selection line coupled to a second circuit block and adapted to select a row of the memory cell within the memory array, wherein the second circuit block is capable of outputting a row turn-off signal when the defect memory cell is detected ;

a sensing amplifier; and

a switch device coupled to the memory cell, a power supply terminal, the sensing amplifier, the column selection line and the row selection line, wherein only when both the column selection line receives a the column turn-off signal and the row selection line receives a the row turn-off signal, the switch device is turned off so ~~that~~ as to disconnect a coupling between a power provided from the power supply terminal and is not coupled to the defect memory cell, thereby breaking the leakage current path existing in the defect memory cell .

2. (original) The device for breaking the leakage current path of claim 1, wherein the switch device further comprises:

a first switch coupled to the memory cell, the power supply terminal and the column selection line, wherein when the column selection line receives the column turn-

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off signal, the first switch is turned off so that the power is not coupled to the memory cell, and when the column selection line does not receive the column turn-off signal, the power is coupled to the memory cell; and

a second switch coupled to the memory cell, the power supply terminal and the row selection line, wherein when the row selection line receives the row turn-off signal, the second switch is turned off so that the power is not coupled to the memory cell, and when the row selection line does not receive the row turn-off signal, the power is coupled to the memory cell.

3. (original) The device for breaking the leakage current path of claim 2, wherein each of the first switch and the second switch comprises a PMOS transistor or PMOSFET transistor.

4. (original) The device for breaking the leakage current path of claim 1, wherein the column turn-off signal and the row turn-off signal are controlled by a stand-by signal.

5. (currently amended) A method for breaking a leakage current path existing in a defect memory cell for a circuit having an memory array, the method comprising:

selecting a column selection line in response to a memory cell within a memory array;

selecting a row selection line in response to the memory cell within the memory array; and

coupling a column turn-off signal to the column selection line and a row turn-off signal to the row selection line when ~~it is determined that~~ the memory cell is defective

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detected to be the defective memory cell and so that a power provided from a power supply terminal is not coupled to the memory cell.

6. (original) The method for breaking the leakage current path of claim 5, wherein the column turn-off signal and the row turn-off signal are controlled by a stand-by signal.

7. (currently amended) A memory device, comprising:

a column selection line coupled to a first circuit block and adapted to select a column of a memory cell within a memory array, wherein the first circuit block is capable of outputting a row turn-off signal when a defect memory cell is detected;

a row selection line coupled to a second circuit block and adapted to select a row of the memory cell within the memory array, wherein the second circuit block is capable of outputting a row turn-off signal when the defect memory cell is detected;

a sensing amplifier; and

a device for breaking a leakage current path, comprising a switch device coupled to the memory cell, a power supply terminal, the sensing amplifier, the column selection line and the row selection line, wherein only when both the column selection line receives a column turn-off signal and the row selection line receives a row turn-off signal, the switch device is turned off so that as to disconnect a coupling between a power provided from the power supply terminal is not coupled to and the defect memory cell, thereby breaking a leakage current path existing in the defect memory cell.

8. (original) The memory device of claim 7, wherein the switch device further comprises:

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a first switch coupled to the memory cell, the power supply terminal and the column selection line, wherein when the column selection line receives the column turn-off signal, the first switch is turned off so that the power is not coupled to the memory cell, and when the column selection line does not receive the column turn-off signal, the power is coupled to the memory cell; and

a second switch coupled to the memory cell, the power supply terminal and the row selection line, wherein when the row selection line receives the row turn-off signal, the second switch is turned off so that the power is not coupled to the memory cell, and when the row selection line does not receive the row turn-off signal, the power is coupled to the memory cell.

9. (original) The memory device of claim 8, wherein each of the first switch and the second switch comprises a PMOS transistor or PMOSFET transistor.

10. (original) The memory device of claim 7, wherein the column turn-off signal and the row turn-off signal are controlled by a stand-by signal.

11. (original) The memory device of claim 7, wherein the memory array comprises a DRAM array.

12. (currently amended) The memory device of claim 7, ~~further comprising a~~
wherein the first circuit block is disposed between an original selection signal and the column selection line for controlling the original selection signal and generating a final column selection signal from a stand-by signal and a fuse signal of the final column selection signal, ~~wherein the first circuit block is coupled to the column selection line.~~

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13. (currently amended) The memory device of claim 7, ~~further comprising a~~
wherein the second circuit block connected to the row selection line for is capable of
generating a final row selection signal from a stand-by signal and a fuse signal of the final
row selection signal.

14. (new) The memory device of claim 12, wherein a state of the fuse signal of the
final column selection signal and a state of the fuse signal of the final row selection signal
for a selected normal memory cell are substantially lower than those of a selected
defective memory cell and the column turn-off signal and the row turn-off signal are
generated in response to the state of the fuse signal of the final column signal and state of
the fuse signal of the row selection signal.